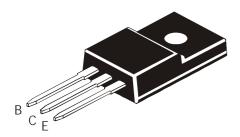
### Continental Device India Limited

An ISO/TS 16949, ISO 9001 and ISO 14001 Certified Company



### NPN/PNP SILICON POWER DARLINGTON TRANSISTORS



TIP122F NPN TIP127F PNP TO-220FP

## Designed for General-Purpose Amplifier and Low-Speed Switching Applications.

### ABSOLUTE MAXIMUM RATINGS(Ta=25deg C)

DESCRIPTION	SYMBOL	VALUE	UNIT
Collector -Base Voltage	VCBO	100	V
Collector -Emitter Voltage	VCEO	100	V
Emitter Base Voltage	VEBO	5.0	V
Collector Current -Continuous	IC	5.0	Α
Collector Current (Peak)	ICM	8.0	Α
Base Current	IB	120	mA
Total Power Dissipation @ Tc=25 deg C	PD	65	W
Derate Above 25 deg C		0.52	W/deg C
Total Power Dissipation @ Ta=25 deg C	PD	2.0	W
Derate Above 25 deg C		0.016	W/deg C
Unclamped Inductive Load Energy (1)	E	50	mj
Junction Temperature	Tj	150	deg C
Storage Temperature Range	Tstg	-65 to +150	deg C
THERMAL RESISTANCE			
From Junction to Ambient	Rth(j-a)	62.5	deg C/W
From Junction to Case	Rth(j-c)	1.92	deg C/W

(1) IC=1A, L=100mH,P.R.F.=10Hz, VCC=20V, RBE=100 ohms

ELECTRICAL CHARACTERISTICS (Ta=25 deg C Unless Specified)						
DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNIT	
Collector Emitter (sus) Voltage	VCEO (sus) *	IC=100mA, IB=0	100	-	V	
Collector Cut off Current	ICBO	VCB=100V, IE=0	-	0.2	mΑ	
	ICEO	IB=O, VCE=50V	-	0.5	mA	
Emitter Cut off Current	IEBO	VEB=5V,IC=0	-	2.0	mΑ	
Collector Emitter Saturation Voltage	VCE(Sat)*	IC=3A, IB=12mA	-	2.0	V	
		IC=5A, IB=20mA	-	4.0	V	
Base Emitter on Voltage	VBE(on) *	IC=3A, VCE=3V	-	2.5	V	
DC Current Gain	hFE*	IC=0.5A, VCE=3V	1.0	-	K	
		IC=3A, VCE=3V	1.0	-	K	

### ELECTRICAL CHARACTERISTICS (Ta=25 deg C Unless Specified)

11P122F/121F					
UNIT					

Output Capacitance

Cob Cob=10V, IE=0, f=0.1MHz

PNP - 300

SYMBOL

/hfe/

TEST CONDITION

IC=3A, VCE=4V

f=1MHz

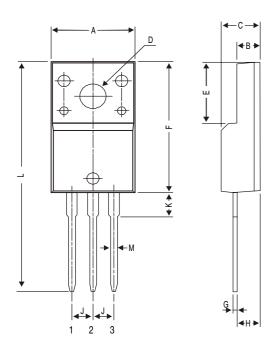
**PNP** - 300 pF **NPN** - 200 pF

\*Pulse test: Pulse Width=300 us; Duty Cycle=2%

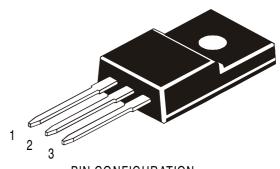
**DESCRIPTION** 

**Small Signal Current Gain** 

# TO-220FP (Fully Isolated) Plastic Package



	DIM	MIN	MAX	
	Α	9.96	10.36	
	В	2.60	3.00	
	С	4.50	4.90	
	D	3.10	3.30	
	Е	7.90	8.20	
	F	16.87	17.27	
Ë.	G	0.45	0.50	
<u>⊒</u>	Н	2.56	2.96	
All diminsions in mm.	J	2.34	2.74	
	K	_	3.08	
	L	_	30.05	
¥	М	_	0.80	



PIN CONFIGURATION

- 1. BASE
- 2. COLLECTOR
- 3. EMITTER

## Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
T0-220FP	200 pcs/polybag 50 pcs/tube	g, = p	3" x 7.5" x 7.5" 3.5" x 3.7" x 21.5"	1.0K 1.0K	17" x 15" x 13.5" 19" x 19" x 19"	16.0K 10.0K	36 kgs 29 kgs

### **Customer Notes**

#### **Disclaimer**

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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